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(71)Applicant : OKI ELECTRIC IND CO LTD

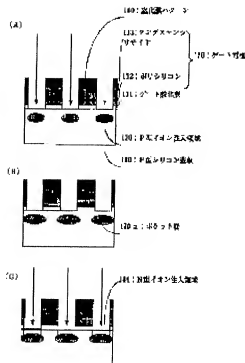
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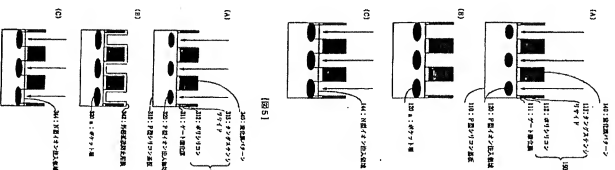
(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

(57) Abstract:

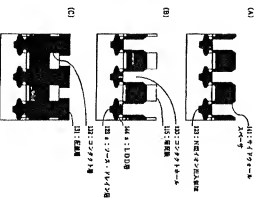
PROBLEM TO BE SOLVED: To permit formation of a MOS FET which reliably has a pocket layer, even when it becomes difficult to implant impurity ions from an oblique direction with respect to a silicon substrate, due to its miniaturization in steps of manufacturing a semiconductor device and in particular, a MOS FET having the pocket layer. **SOLUTION:** A gate oxide film 111, a gate electrode 150 made of a polysilicon film 112 and a tungsten silicide film 113, and a nitride film pattern 140 are selectively formed on a P-type silicon substrate 110, and then the P-type silicon substrate is subjected to vertical implantation of P-type impurity ions with respect to the substrate. Then a P-type ion implanted region 120 formed by the P-type ion implantation is diffused and activated, to form a pocket layer 120a prior to the formation of other ion-implanted regions.



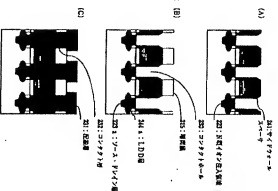
[図1]



[図2]



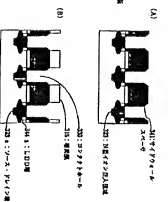
[図4]



[図3]



[図6]



[図7]

